

#### ABSTRACT OF THE DISCLOSURE

A semiconductor device comprising: a base substrate including a semiconductor substrate 10 and a semiconductor element formed on the semiconductor substrate 10; an insulation film 22, 24, 26 formed on the base substrate having an opening 30, 32; and a metal interconnection 42 formed buried in the opening 30, 32 including: a barrier layer 34 formed on an inside wall and a bottom of the opening 30, 32; an adhesion layer 36 containing zirconium formed on the barrier layer 34; and a metal interconnection material 38, 40 containing copper as a main component formed on the barrier layer 36. Whereby the peeling of the copper interconnection in the fabrication process can be prevented. The electro migration resistance and stress migration resistance of the copper interconnection can be further improved.